

ABSTRACT OF THE DISCLOSURE

A method for manufacturing a silicon carbide single crystal includes the steps of: setting a substrate as a seed crystal in a reactive chamber; introducing a raw material gas into the reactive chamber; growing a silicon carbide single crystal from the substrate; heating the gas at an upstream side from the substrate in a gas flow path; keeping a temperature of the substrate at a predetermined temperature lower than the gas so that the single crystal is grown from the substrate; heating a part of the gas, which is a non-reacted raw material gas and does not contribute to crystal growth, after passing through the substrate; and absorbing a non-reacted raw material gas component in the non-reacted raw material gas with an absorber.